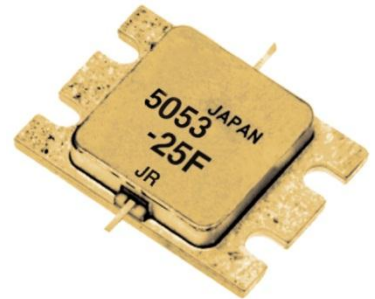


FEATURES

- High Output Power: $P_{1dB} = 44.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 8.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 39\%$ (Typ.)
- Low IM3 = $-46\text{dBc}@P_o = 33.5\text{dBm}$
- Broad Band: 5.0 to 5.3GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$



DESCRIPTION

The FLM5053-25F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	93.7	W
Storage Temperature	T_{stq}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 64.0 and -11.2 mA respectively with gate resistance of 25ohm.

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	11.6	17.4	A
Transconductance	g_m	$V_{DS}=5V, I_{DS}=6800\text{mA}$	-	5800	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=600\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-600\text{uA}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$	43.5	44.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}	$I_{DS}=0.55 I_{DSS}$ (Typ.),	7.5	8.5	-	dB
Drain Current	I_{dsr}	$f=5.0$ to 5.3 GHz,	-	6200	7600	mA
Power-added Efficiency	η_{add}	$Z_S=Z_L=50\text{ohm}$	-	39	-	%
Gain Flatness	ΔG		-	-	+/-0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 5.3$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 33.5\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	1.4	1.6	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	100	deg.C

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

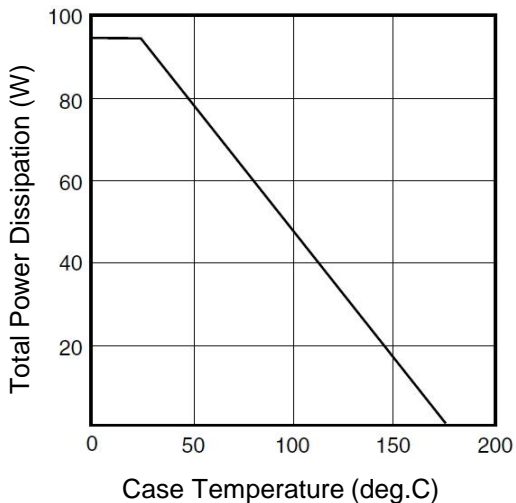
CASE STYLE	IK
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ESD	Class 3A	4000V to 8000V
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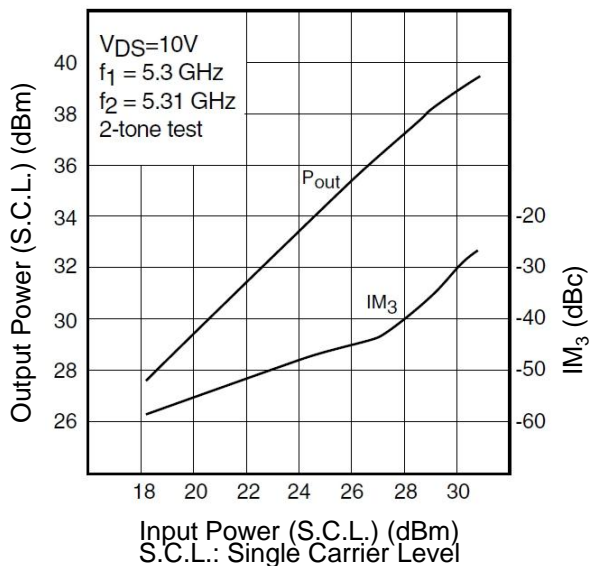
Note : Based on EIAJ ED-4701 C-111A (C=100pF, R=1.5kohm)

RoHS Compliance	Yes
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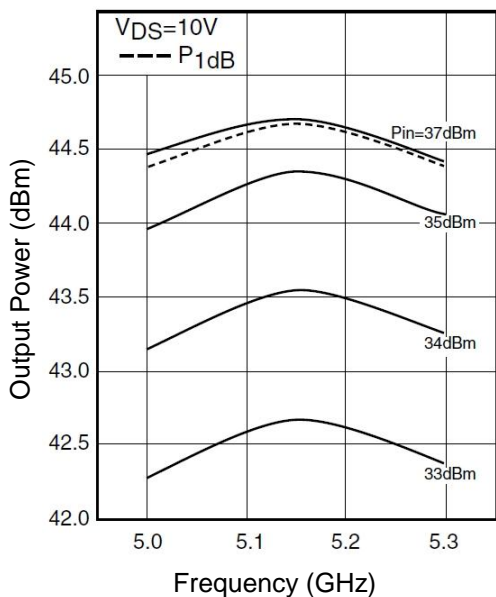
POWER DERATING CURVE



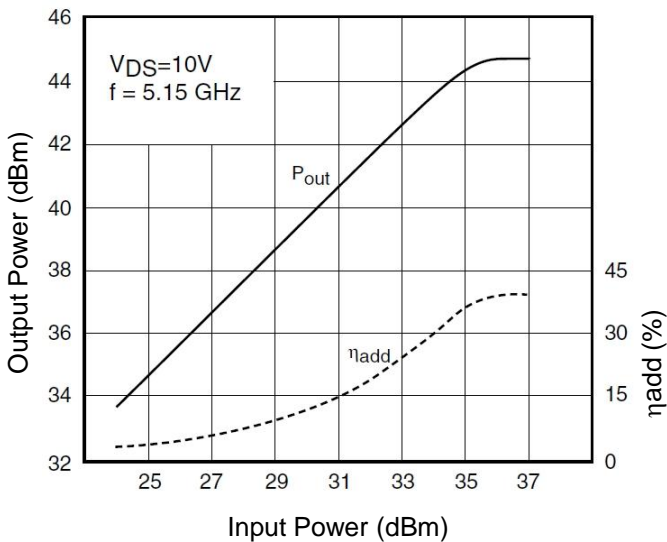
OUTPUT POWER & IM₃ vs. INPUT POWER

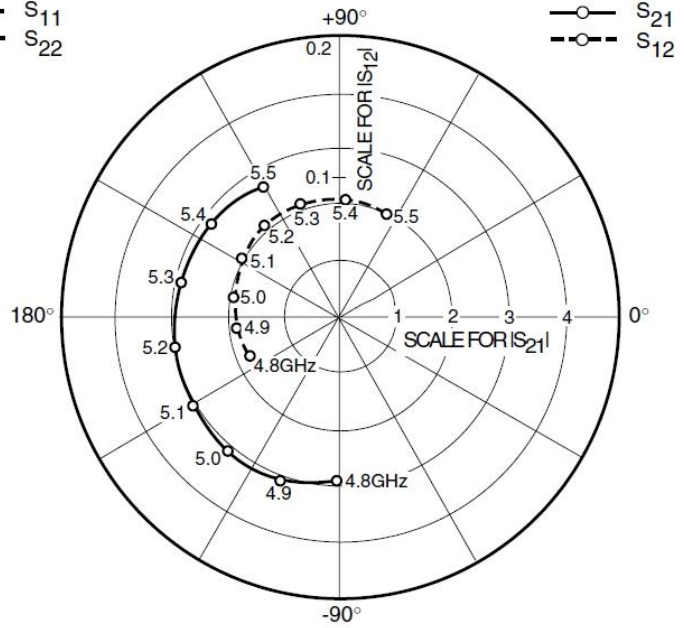
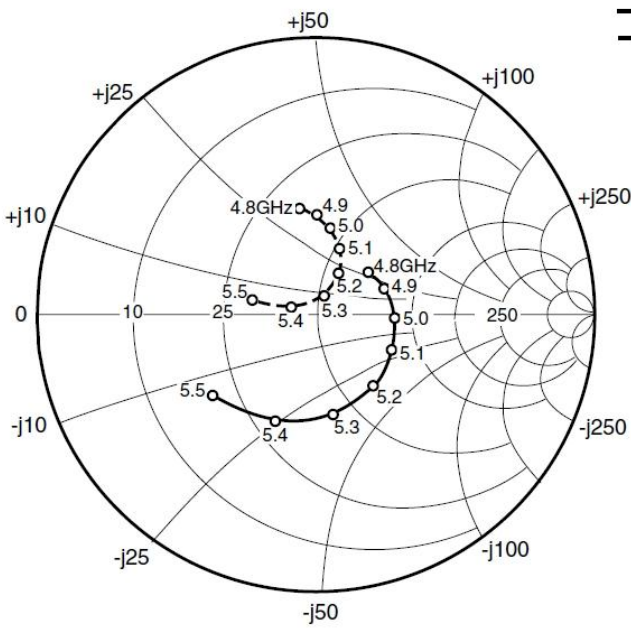


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER, η_{add} vs. INPUT POWER



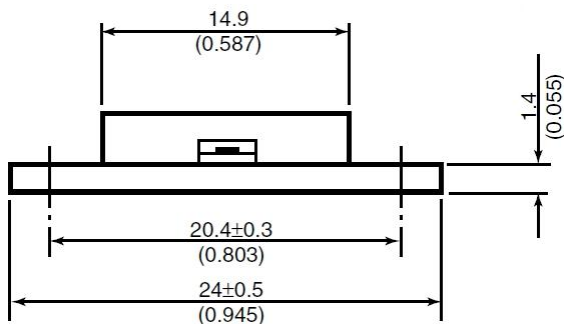
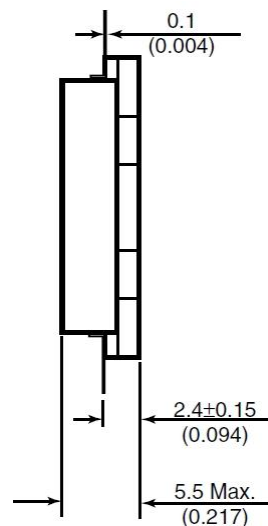
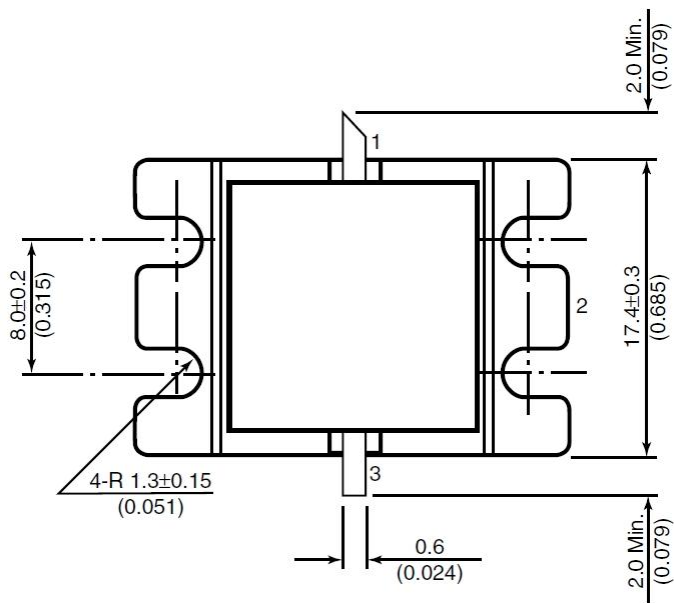


S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 6800mA$

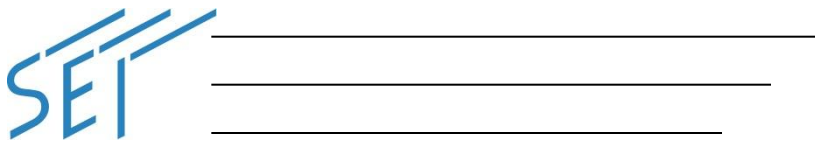
FREQUENCY (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
4800	0.239	37.6	2.884	-92.0	0.070	-155.8	0.381	99.0
4900	0.258	17.9	3.143	-110.7	0.076	-174.0	0.358	88.4
5000	0.284	-5.6	3.096	-129.9	0.078	169.1	0.314	78.5
5100	0.306	-27.2	3.059	-149.5	0.082	150.1	0.247	68.2
5200	0.344	-52.9	3.023	-170.3	0.084	130.7	0.166	58.1
5300	0.375	-80.6	2.966	168.0	0.085	109.7	0.067	64.5
5400	0.425	-110.2	2.844	144.6	0.083	86.9	0.090	167.2
5500	0.471	-141.4	2.636	120.9	0.079	64.5	0.239	169.8

Case Style "IK"
Metal-Ceramic Hermetic Package



1. Gate
2. Source (Flange)
3. Drain

Unit: mm(inches)



FLM5053-25F
C-Band Internally Matched FET

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.